Supplementary Information for:

Electrohydrodynamic-jet Printed Zinc-Tin Oxide TFTs and Their Bias Stability

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		At% at 400 °C		At% at 500 °C		
O _M /O _M +O _{vac} +O _{OH}		63.57		64.68		
	400 °C		500 ℃	400 ℃	500°C	
	Peak B.E.		Peak B.E.	At%	At%	
O 1s (O _M)	530.24 eV		529.98 eV	39.93	37.99	
O 1s (O _{VAC})	531.54 eV		531.39 eV	18.57	16.02	
O 1s (O _{OH})	532.49 eV		533.04 eV	4.31	4.72	
Sn 3d _{5/2}	Approximately 486.2 eV			24.61	23.34	
Zn 2p _{3/2}	Approximately 1022.5 eV			12.58	17.92	
O _{vac} /O _M +O _{vac} +O _{OH}		29.56		27.27		
O _{OH} /O _M +O _{vac} +O _{OH}		6.86			8.03	

Table S1. O 1s, Sn 3d and Zn 2p core shells in XPS data and the deconvoluted O 1s core shell of EDH-jet printed ZTO thin film



Figure S1. Contact angle measurements of gate insulator surfaces with (a) before UV/O_3 treatment, (b) after UV/O_3 treatment.



Figure S2. OM image and thickness morphology of EHD-jet printed ZTO lines with various ZTO concentrations (a) 0.1M, (b) 0.3M and (c) 0.5M.



Figure S3. AFM images of surface morphology of the ZTO thin films with fabrication methods; (a) spin coating, (b) EHD printing.